N-Channel 400-V (D-S) MOSFET

Key Features:

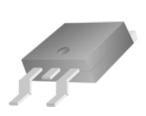
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

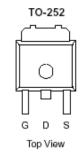
Typical	Applications:
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- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
400	1000 @ V _{GS} = 10V	10 ^a	
400	1010 @ V _{GS} = 6.5V	10	







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			400	V		
Gate-Source Voltage			±20	V		
Continuous Drain Current a	T _C =25°C	I_D	10	Α		
Pulsed Drain Current ^b		I _{DM}	40	Α		
Continuous Source Current (Diode Conduction) a			10	Α		
Power Dissipation ^a	T _C =25°C	P_{D}	50	W		
Operating Junction and Storage Temperature Range	·	T_J, T_{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

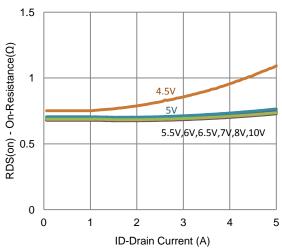
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current		$V_{DS} = 320 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 320 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uД
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	12.5			Α
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_{D} = 5 \text{ A}$			1000	mΩ
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 6.5 \text{ V}, I_D = 4 \text{ A}$			1010	11122
Forward Transconductance ^a	g _{fs}	$V_{DS} = 50 \text{ V}, I_{D} = 5 \text{ A}$		6		S
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 5 \text{ A}, V_{GS} = 0 \text{ V}$		0.81		V
		Dynamic ^b				
Total Gate Charge	Q_g	$V_{DS} = 100 \text{ V}, V_{GS} = 6.5 \text{ V},$		17		
Gate-Source Charge	Q_gs	$I_{D} = 1 \text{ A}$		6.8		nC
Gate-Drain Charge	Q_{gd}	10 - 1 7X		5.6		
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 100 \text{ V}, R_{L} = 100 \Omega,$		11		
Rise Time	t _r	$I_{D} = 1 \text{ A},$		5		nc
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		29		ns
Fall Time	t _f	VGEN = 10 V, NGEN 0 12		8		
Input Capacitance	C _{iss}			1265		
Output Capacitance	C _{oss}	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		43		pF
Reverse Transfer Capacitance	C_{rss}			27		

Notes

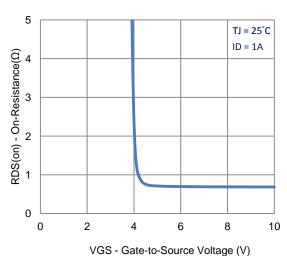
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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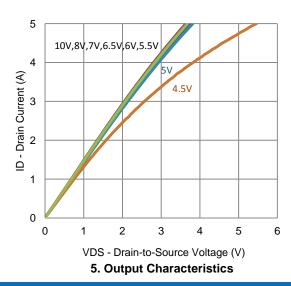
Typical Electrical Characteristics

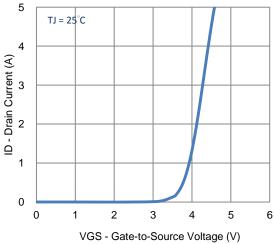


1. On-Resistance vs. Drain Current

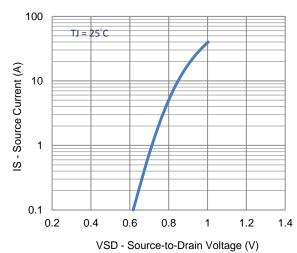


3. On-Resistance vs. Gate-to-Source Voltage

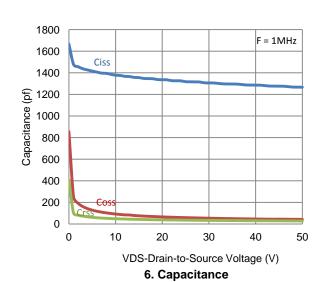




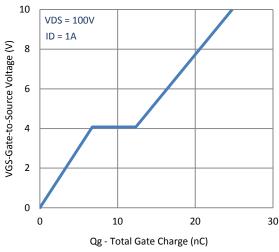




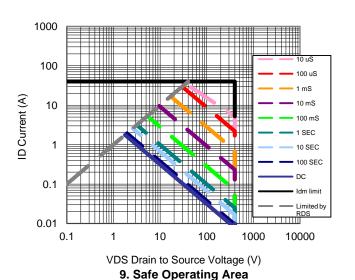
4. Drain-to-Source Forward Voltage

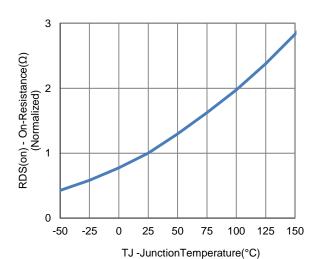


Typical Electrical Characteristics

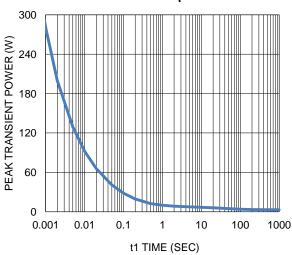


7. Gate Charge

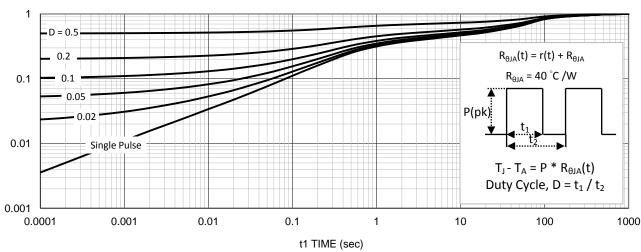




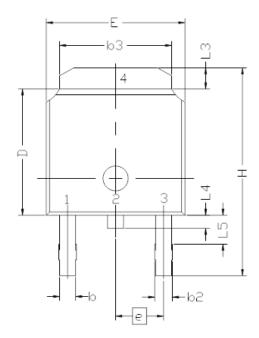
8. Normalized On-Resistance Vs **Junction Temperature**

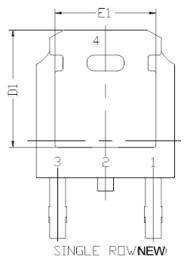


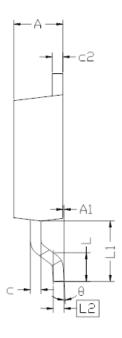
10. Single Pulse Maximum Power Dissipation



Package Information







	DIMENS:	I IANDI	REQMTS
SYMBOL	MIN	NOM	MAX
E	6.40	6.60	6.731
L		1.52	1.77
L1		.743 RI	
	0.	.508 BS	
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0,88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
е		286 BS	C.
Α	2,20	2.30	2,38
A1	0		0.127
	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5,30		
E1	4.40		
θ	0*		10°

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.